L Number	Hits	Search Text	DB	Time stamp
1	775006	semiconductor	USPAT;	2004/03/12 12:43
			US-PGPUB;	
			EPO; JPO	
2	520	semiconductor and(sacrificial disposable	USPAT;	2004/03/12 12:46
		expandable temporary) same (bottom base	US-PGPUB;	
		lower) near7 (opening\$1 groove\$1 trench\$2	EPO; JPO	
	,	hole\$1 aperture\$1)same substrate		
3	245	(semiconductor and(sacrificial disposable	USPAT;	2004/03/12_12:46
		expandable temporary) same (bottom base	US-PGPUB;	
		lower) near7 (opening\$1 groove\$1 trench\$2	EPO; JPO	
		hole\$1 aperture\$1)same substrate) and		
1		etch\$3 near3 (stop\$4 inhibit\$3 prevent\$3		
		resist\$3)		
4	88	, ,	USPAT;	2004/03/12 12:48
		expandable temporary) same (bottom base	US-PGPUB;	
		lower) near7- (opening\$1 groove\$1 trench\$2	EPO; JPO	
1		hole\$1 aperture\$1) same substrate) and		
1		etch\$3 near3 (stop\$4 inhibit\$3 prevent\$3		
		resist\$3)) and (protect\$3 prevent\$3		
		inhibit\$3) near10 (bottom base lower)		